# **MA MOSPEC**

## **Ultra Fast Recovery Rectifier Diodes**

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- \* High Surge Capacity
- \* Low Power Loss, High efficiency
- \* Glass Passivated chip junctions
- \* 150 °C Operating Junction Temperature
- \* Low Stored Charge Majority Carrier Conduction
- \* Low Forward Voltage, High Current Capability
- \* High-Switching Speed 50 Nanosecond Recovery Time
- \* Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

#### **MAXIMUM RATINGS**

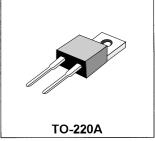
Characteristic	Symbol	U10A				Unit
		30	40	50	60	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	300	400	500	600	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	210	280	350	420	٧
Average Rectifier Forward Current	I <sub>F(AV)</sub>	10			Α	
Non-Repetitive Peak Surge Current ( Surge applied at rate load conditions halfware,single phase,60Hz )	  FSM	175			А	
Operating and Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	- 65 to + 150			°C	

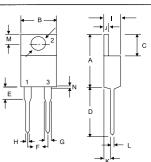
### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol		U1	Unit		
		30	40	50	60	
Maximum Instantaneous Forward Voltage $(I_F = 10 \text{ Amp}, T_C = 25 ^{\circ}\text{C})$ $(I_F = 10 \text{ Amp}, T_C = 100 ^{\circ}\text{C})$	V <sub>F</sub>	1.30 1.15		1.50 1.36		V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_c = 25$ °C) (Rated DC Voltage, $T_c = 100$ °C)	I <sub>R</sub>	10 500		uA		
Reverse Recovery Time ( I <sub>F</sub> = 0.5 A, I <sub>R</sub> =1.0 A, I <sub>rr</sub> =0.25 A)	T <sub>rr</sub>	50		ns		
Typical Junction Capacitance ( Reverse Voltage of 4 volts & f=1 MHz)	C <sub>P</sub>	70		pF		

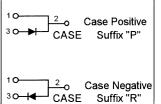
ULTRA FAST RECTIFIERS

10 AMPERES 300 -- 600 VOLTS





	MILLMETERS			
OIM	MIN	MAX		
A B	14.68 9.78	15.32 10.42		
C	6.01	6.52		
D E	13.06 3.57	14.62 4.07		
F	4.83	5.33		
G	1.12	1.36		
H	0.72 4.22	0.96 4.98		
j	1.14	1.36		
K	2.20	2.97		
L M	0.33 2.48	0.55 2.98		
N		1.00		
0	3.70	3.90		



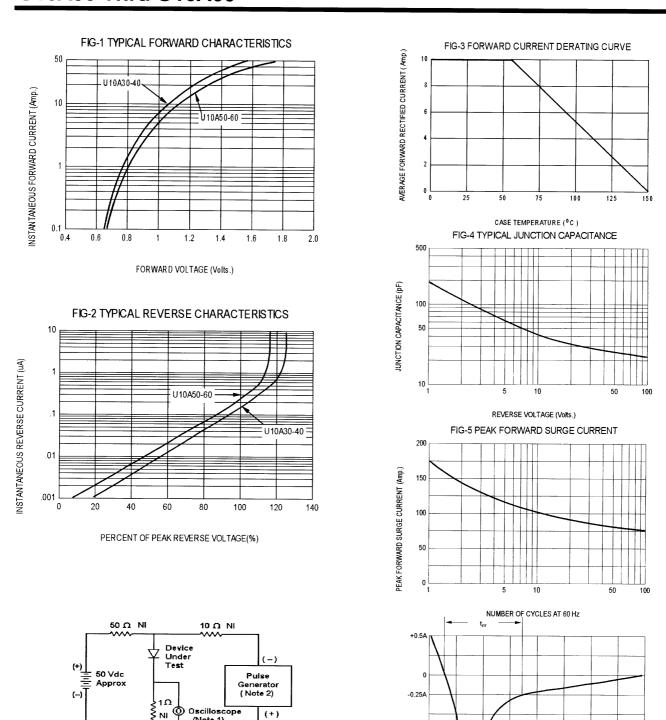


Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram

Set time base for 10/20 ns/div

(Note 1)

Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M  $\Omega$  , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50  $\Omega$ 



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